

MOTOROLA
SEMICONDUCTOR
 TECHNICAL DATA

1N3899 thru 1N3903
MR1386

1N3901 and MR1386 are
 Motorola Preferred Devices

Designers Data Sheet

STUD MOUNTED
FAST RECOVERY POWER RECTIFIERS

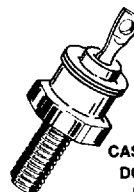
... designed for special applications such as dc power supplies, inverters, converters, ultrasonic systems, choppers, low RF interference, sonar power supplies and free wheeling diodes. A complete line of fast recovery rectifiers having typical recovery time of 150 nanoseconds providing high efficiency at frequencies to 250 kHz.

Designers Data for "Worst Case" Conditions

The Designers Data sheets permit the design of most circuits entirely from the information presented. Limit curves — representing boundaries on device characteristics — are given to facilitate "worst case" design.

FAST RECOVERY
POWER RECTIFIERS

50-600 VOLTS
 20 AMPERES



CASE 42A-01
 DO-203AB
 METAL

3

MECHANICAL CHARACTERISTICS

CASE: Welded, hermetically sealed
FINISH: All external surfaces corrosion resistant and readily solderable
POLARITY: Cathode to Case
WEIGHT: 17 grams (approximately)
MOUNTING TORQUE: 25 in-lb max

***MAXIMUM RATINGS**

Rating	Symbol	1N3899	1N3900	1N3901	1N3902	1N3903	MR1386	Unit
Peak Repetitive Reverse Voltage	V _{RRM}							Volts
Working Peak Reverse Voltage	V _{RWM}	50	100	200	300	400	600	
DC Blocking Voltage	V _R							
Non-Repetitive Peak Reverse Voltage	V _{RSM}	75	150	250	350	450	650	Volts
RMS Reverse Voltage	V _{R(RMS)}	35	70	140	210	280	420	Volts
Average Rectified Forward Current (Single phase, resistive load, T _C = 100°C)	I _O	← 20 →						Amps
Non-Repetitive Peak Surge Current (surge applied at rated load conditions)	I _{FSM}	← 250 (one cycle) →						Amps
Operating Junction Temperature Range	T _J	← -65 to +150 →						°C
Storage Temperature Range	T _{stg}	← -65 to +175 →						°C

***THERMAL CHARACTERISTICS**

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	R _{θJC}	1.8	°C/W

***ELECTRICAL CHARACTERISTICS**

Characteristic	Symbol	Min	Typ	Max	Unit
Instantaneous Forward Voltage (I _F = 63 Amp, T _J = 150°C)	V _F	—	1.2	1.5	Volts
Forward Voltage (I _F = 20 Amp, T _C = 25°C)	V _F	—	1.1	1.4	Volts
Reverse Current (rated dc voltage) T _C = 25°C	I _R	—	10	50	μA
T _C = 100°C		—	0.5	6.0	mA

***REVERSE RECOVERY CHARACTERISTICS**

Characteristic	Symbol	Min	Typ	Max	Unit
Reverse Recovery Time (I _F = 1.0 Amp to V _R = 30 Vdc, Figure 16)	t _{rr}	—	150	200	ns
(I _{FM} = 36 Amp, di/dt = 25 A/μs, Figure 17)		—	200	400	
Reverse Recovery Current (I _F = 1.0 Amp to V _R = 30 Vdc, Figure 16)	I _{RM(REC)}	—	—	3.0	Amp

*Indicates JEDEC Registered Data for 1N3899 Series

FIGURE 1 - FORWARD VOLTAGE

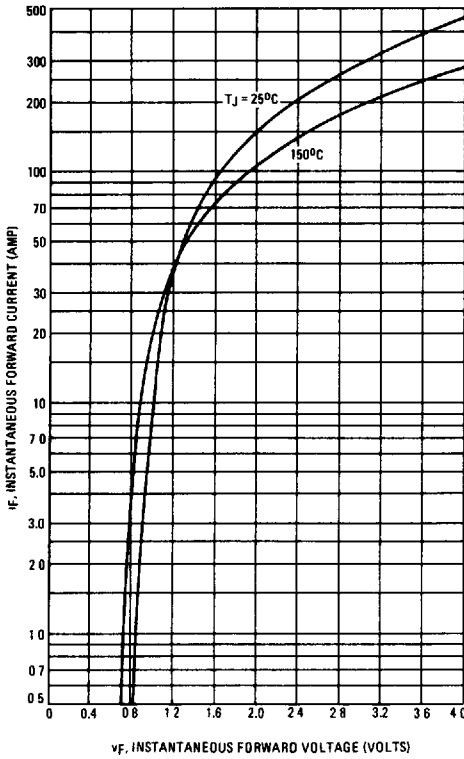
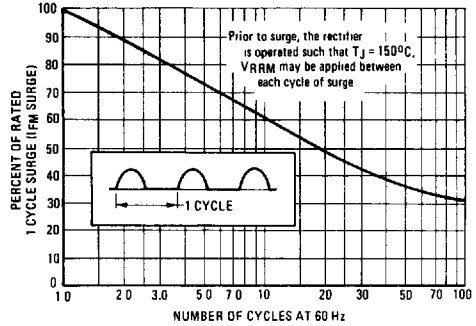
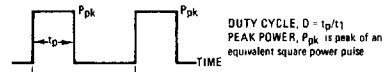


FIGURE 2 - MAXIMUM SURGE CAPABILITY



NOTE 1



To determine maximum junction temperature of the diode in a given situation, the following procedure is recommended:

The temperature of the case should be measured using a thermocouple placed on the case at the temperature reference point (see Note 3). The thermal mass connected to the case is normally large enough so that it will not significantly respond to heat surges generated in the diode as a result of pulsed operation once steady state conditions are achieved. Using the measured value of T_C , the junction temperature may be determined by

$$T_J = T_C + \Delta T_{JC}$$

where ΔT_{JC} is the increase in junction temperature above the case temperature. It may be determined by

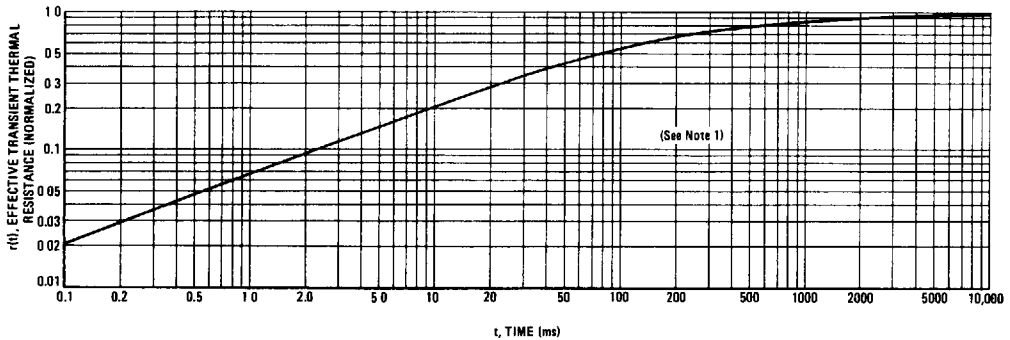
$$\Delta T_{JC} = P_{pk} R_{\theta JC} [D + (1 - D) r(t_1 + t_p) + r(t_p) - r(t_1)]$$

where

$r(t)$ = normalized value of transient thermal resistance at time, t , from Figure 3, i.e.

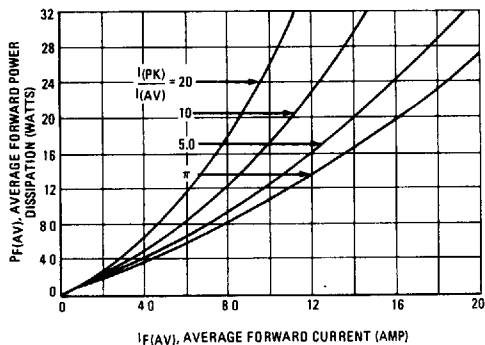
$r(t_1 + t_p)$ = normalized value of transient thermal resistance at time $t_1 + t_p$.

FIGURE 3 - THERMAL RESPONSE



SINE WAVE INPUT

FIGURE 4 - FORWARD POWER DISSIPATION



SQUARE WAVE INPUT

FIGURE 5 - FORWARD POWER DISSIPATION

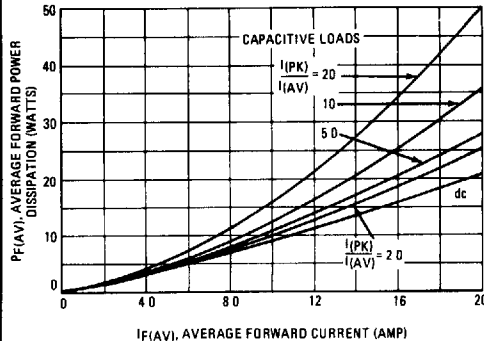


FIGURE 6 - CURRENT DERATING

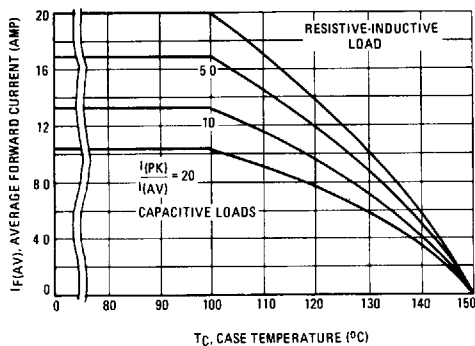


FIGURE 7 - CURRENT DERATING

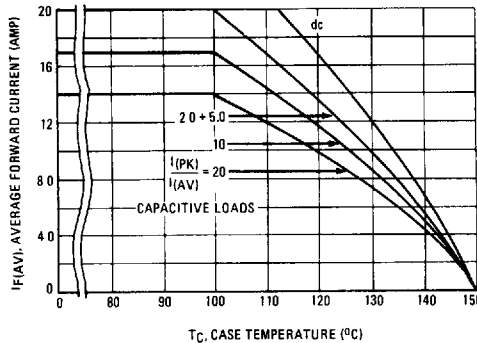


FIGURE 8 - TYPICAL REVERSE CURRENT

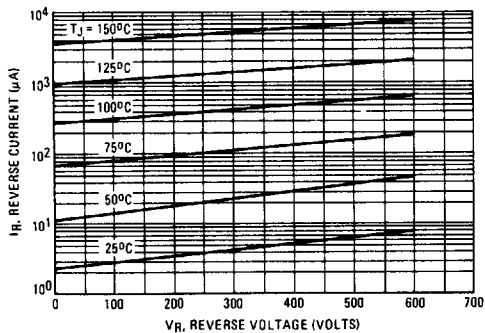
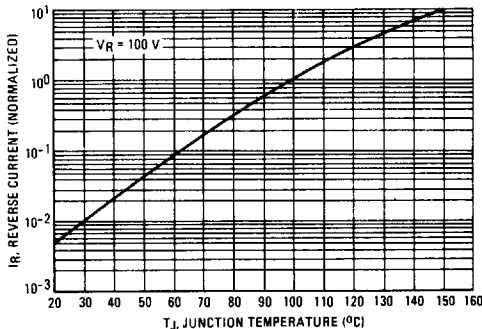


FIGURE 9 - NORMALIZED REVERSE CURRENT



3

TYPICAL DYNAMIC CHARACTERISTICS

FIGURE 10 - FORWARD RECOVERY TIME

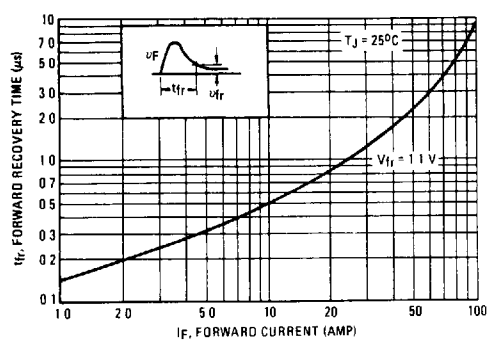
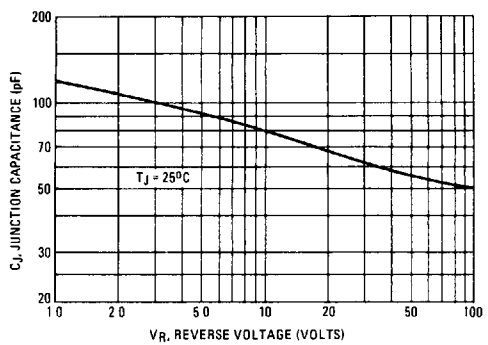


FIGURE 11 - JUNCTION CAPACITANCE



TYPICAL RECOVERED STORED CHARGE DATA

(See Note 2)

FIGURE 12 - $T_J = 25^\circ C$

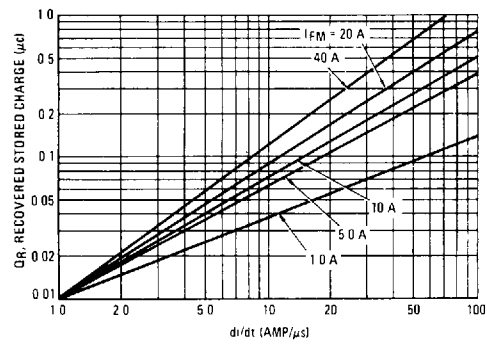
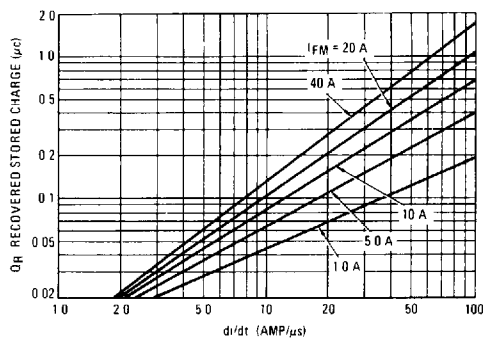


FIGURE 13 - $T_J = 75^\circ C$



STORED CHARGE DATA

FIGURE 14 - $T_J = 100^\circ C$

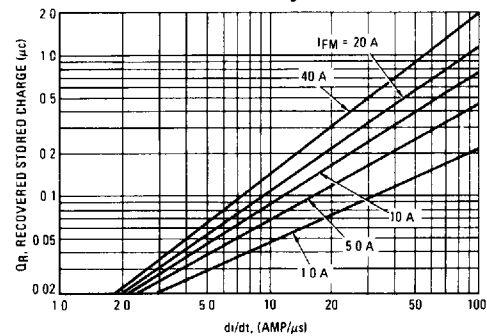
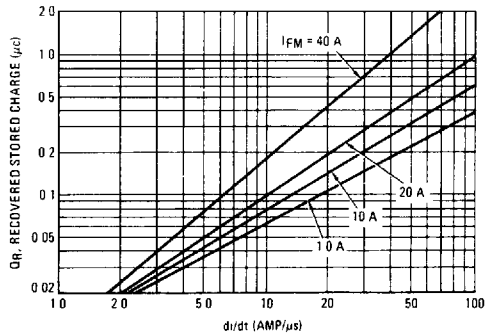
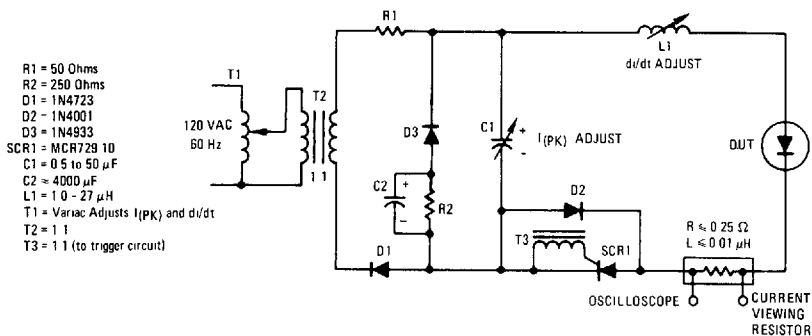


FIGURE 15 - $T_J = 150^\circ C$



3

FIGURE 16 — JEDEC REVERSE RECOVERY CIRCUIT



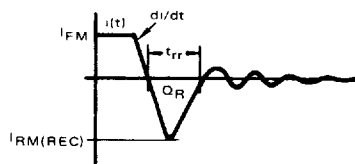
NOTE 2

Reverse recovery time is the period which elapses from the time that the current, thru a previously forward biased rectifier diode, passes thru zero going negatively until the reverse current recovers to a point which is less than 10% peak reverse current.

Reverse recovery time is a direct function of the forward current prior to the application of reverse voltage.

For any given rectifier, recovery time is very circuit dependent. Typical and maximum recovery time of all Motorola fast recovery power rectifiers are rated under a fixed set of conditions using $I_F = 1.0 \text{ A}$, $V_R = 30 \text{ V}$. In order to cover all circuit conditions, curves are given for typical recovered stored charge versus commutation di/dt for various levels of forward current and for junction temperatures of 25°C, 75°C, 100°C, and 150°C.

To use these curves, it is necessary to know the forward current level just before commutation, the circuit commutation di/dt , and the operating junction temperature. The reverse recovery test current waveform for all Motorola fast recovery rectifiers is shown.



From stored charge curves versus di/dt , recovery time (t_{rr}) and peak reverse recovery current ($I_{RM(REC)}$) can be closely approximated using the following formulas:

$$t_{rr} = 1.41 \times \left[\frac{Q_R}{di/dt} \right]^{1/2}$$

$$I_{RM(REC)} = 1.41 \times \left[Q_R \times di/dt \right]^{1/2}$$